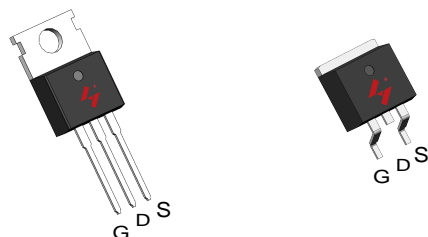


N-Channel Enhancement Mode MOSFET

Features

- 30V/100A
 $R_{DS(ON)} = 3.5m\Omega$ (typ.) @ $V_{GS} = 10V$
- 100% EAS Guaranteed
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Pin Description

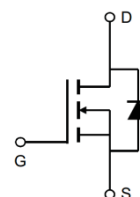


TO-220FB-3L

TO-263-2L

Applications

- High Frequency Synchronous Buck Converters for Computer Processor Power
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use



N-Channel MOSFET

Ordering and Marking Information

| | | |
|--|--|---|
|  P HY3003 YYXXXJWW G |  B HY3003 YYXXXJWW G | Package Code P : TO-220FB-3L B: TO-263-2L Date Code YYXXX WW Assembly Material G : Lead Free Device |
|--|--|---|

Note: HUAYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate Termination finish; which are fully compliant with RoHS. HUAYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUAYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUAYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.

Absolute Maximum Ratings

| Symbol | Parameter | Rating | Unit | |
|--|--|-------------------------|------------------|---------------------------|
| Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted) | | | | |
| V_{DSS} | Drain-Source Voltage | 30 | V | |
| V_{GSS} | Gate-Source Voltage | ± 20 | | |
| T_J | Maximum Junction Temperature | 150 | $^\circ\text{C}$ | |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ | |
| I_S | Diode Continuous Forward Current | $T_C=25^\circ\text{C}$ | 100 | A |
| Mounted on Large Heat Sink | | | | |
| I_{DM} | Pulsed Drain Current * | $T_C=25^\circ\text{C}$ | 380** | A |
| I_D | Continuous Drain Current | $T_C=25^\circ\text{C}$ | 100 | A |
| | | $T_C=100^\circ\text{C}$ | 68 | |
| P_D | Maximum Power Dissipation | $T_C=25^\circ\text{C}$ | 71 | W |
| | | $T_C=100^\circ\text{C}$ | 28.6 | |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case | | 1.75 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance-Junction to Ambient | | 62.5 | $^\circ\text{C}/\text{W}$ |
| E_{AS} | Avalanche Energy, Single Pulsed | $L=0.5\text{mH}$ | 200*** | mJ |

Note : * Repetitive rating ; pulse width limited by junction temperature

** Drain current is limited by junction temperature

*** $V_D=24\text{V}$

Electrical Characteristics ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

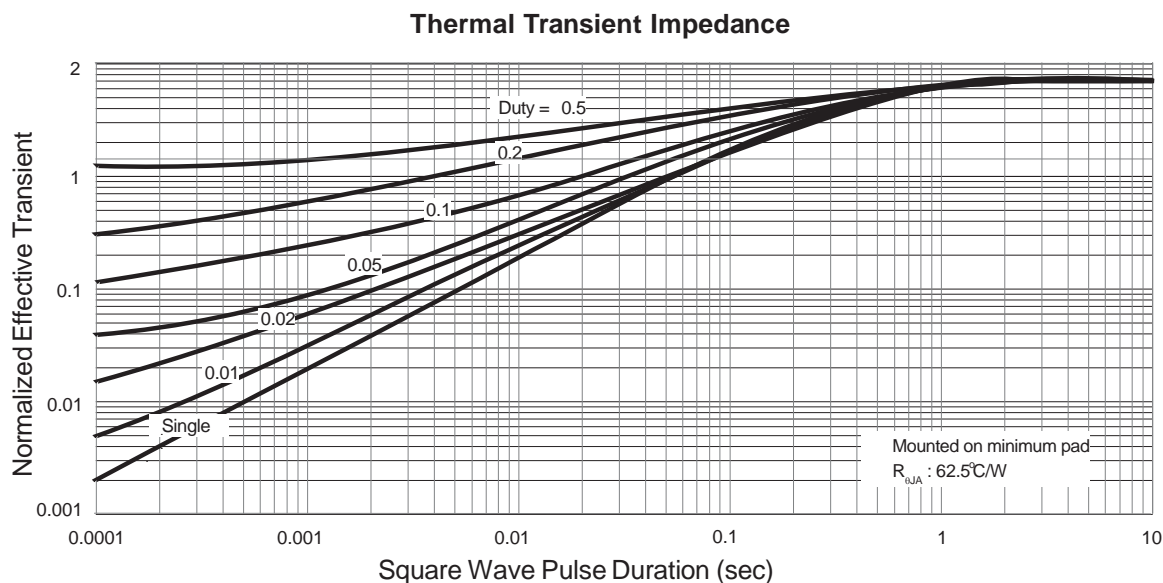
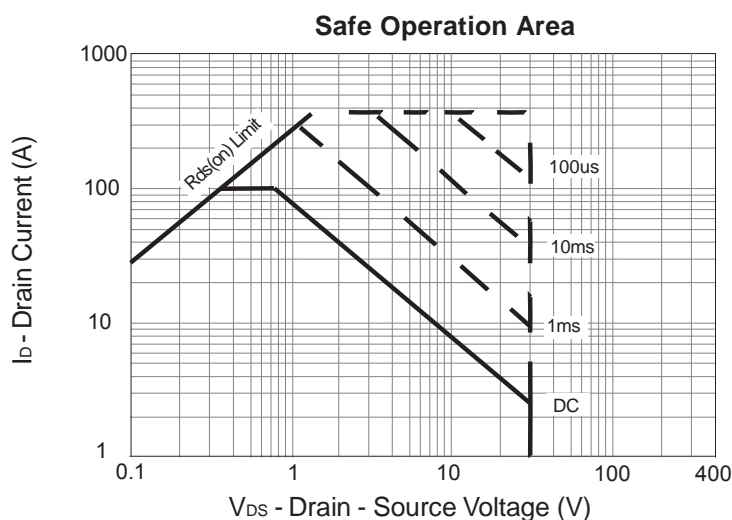
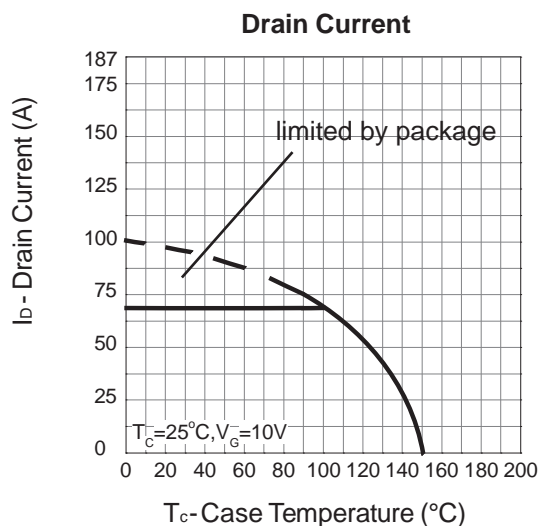
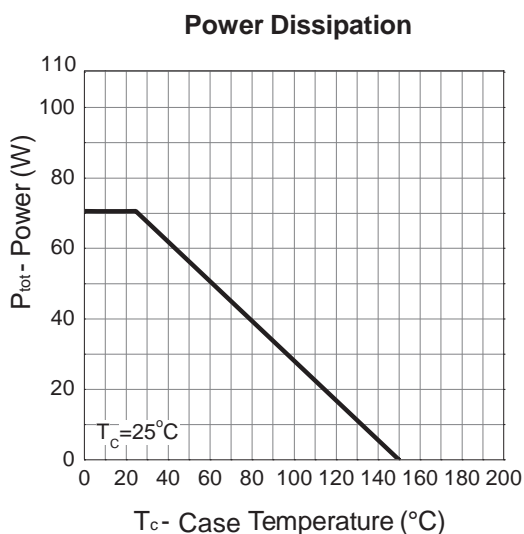
| Symbol | Parameter | Test Conditions | HY3003 | | | Unit |
|-------------------------------|----------------------------------|---|--------|------|-----------|------------------|
| | | | Min. | Typ. | Max. | |
| Static Characteristics | | | | | | |
| BV_{DSS} | Drain-Source Breakdown Voltage | $V_{GS}=0\text{V}, I_{DS}=250\mu\text{A}$ | 30 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS}=30\text{V}, V_{GS}=0\text{V}$ $T_J=85^\circ\text{C}$ | - | - | 1 | μA |
| | | | - | - | 30 | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$ | 1 | 1.6 | 2 | V |
| I_{GSS} | Gate Leakage Current | $V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$ | - | - | ± 100 | nA |
| $R_{DS(ON)}^*$ | Drain-Source On-state Resistance | $V_{GS}=10\text{V}, I_{DS}=50\text{A}$ | - | 3.5 | 5.0 | $\text{m}\Omega$ |
| | | $V_{GS}=4.5\text{V}, I_{DS}=50\text{A}$ | - | 4.7 | 7.0 | $\text{m}\Omega$ |
| Diode Characteristics | | | | | | |
| V_{SD}^* | Diode Forward Voltage | $I_{SD}=50\text{A}, V_{GS}=0\text{V}$ | - | 0.8 | 1.0 | V |
| t_{rr} | Reverse Recovery Time | $I_{DS}=50\text{A}, di_{SD}/dt=100\text{A}/\mu\text{s}$ | - | 14 | - | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 5 | - | nC |

Electrical Characteristics (Cont.) ($T_c = 25^\circ\text{C}$ Unless Otherwise Noted)

| Symbol | Parameter | Test Conditions | HY3003 | | | Unit |
|------------------------------------|------------------------------|---|--------|------|------|----------|
| | | | Min. | Typ. | Max. | |
| Dynamic Characteristics | | | | | | |
| R_G | Gate Resistance | $V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$ | - | 1.2 | - | Ω |
| C_{iss} | Input Capacitance | $V_{GS}=0V,$ $V_{DS}=25V,$ Frequency=1.0MHz | - | 3267 | - | pF |
| C_{oss} | Output Capacitance | | - | 762 | - | |
| C_{rss} | Reverse Transfer Capacitance | | - | 288 | - | |
| $t_{d(ON)}$ | Turn-on Delay Time | $V_{DD}=15V, R_G=3.3\Omega,$ $I_{DS}=50A, V_{GS}=10V,$ | - | 7.8 | 9.8 | ns |
| T_r | Turn-on Rise Time | | - | 15 | 18.8 | |
| $t_{d(OFF)}$ | Turn-off Delay Time | | - | 37.3 | 47 | |
| T_f | Turn-off Fall Time | | - | 10.6 | 13.3 | |
| Gate Charge Characteristics | | | | | | |
| Q_g | Total Gate Charge | $V_{DS}=24V, V_{GS}=10V,$ $I_{DS}=50A$ | - | 67 | - | nC |
| Q_{gs} | Gate-Source Charge | | - | 5 | - | |
| Q_{gd} | Gate-Drain Charge | | - | 16 | - | |

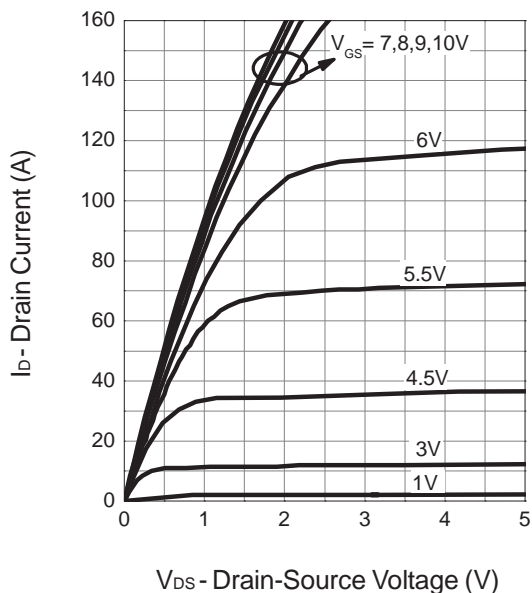
Note * : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

Typical Operating Characteristics

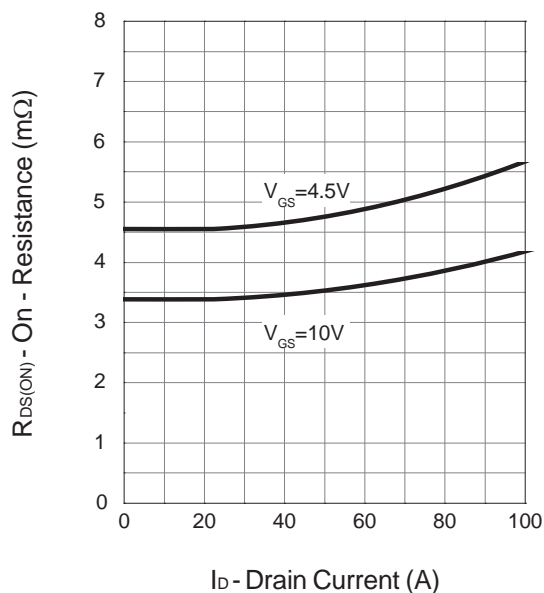


Typical Operating Characteristics (Cont.)

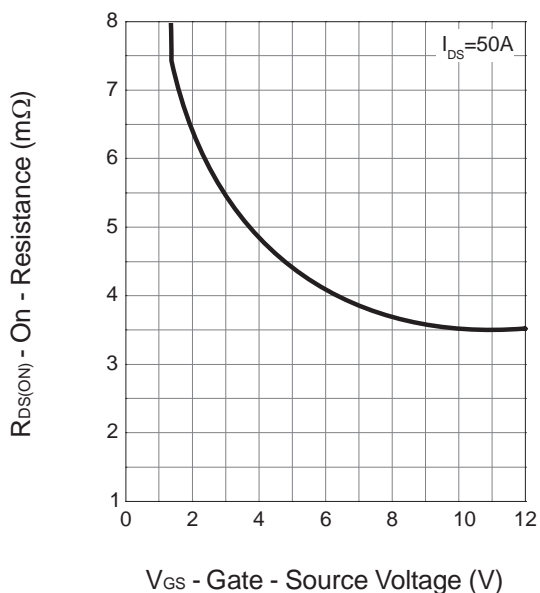
Output Characteristics



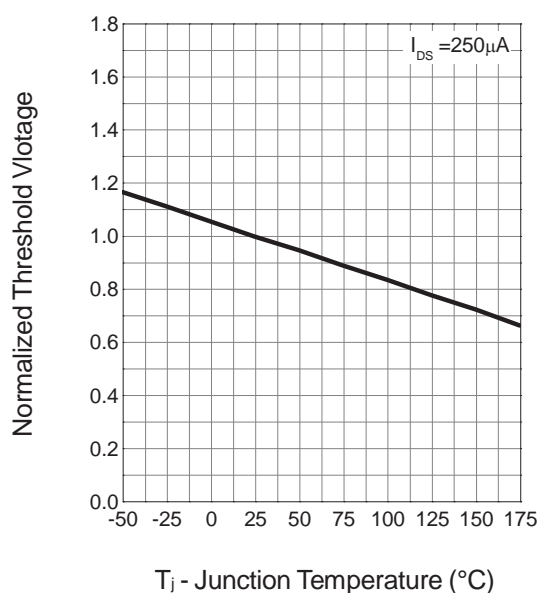
Drain-Source On Resistance



Drain-Source On Resistance

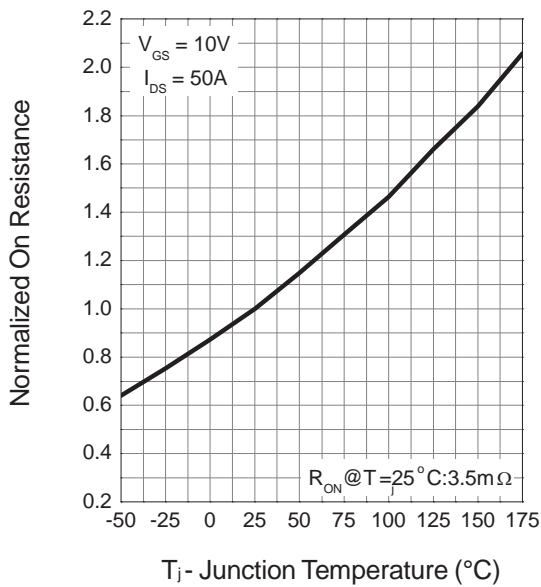


Gate Threshold Voltage

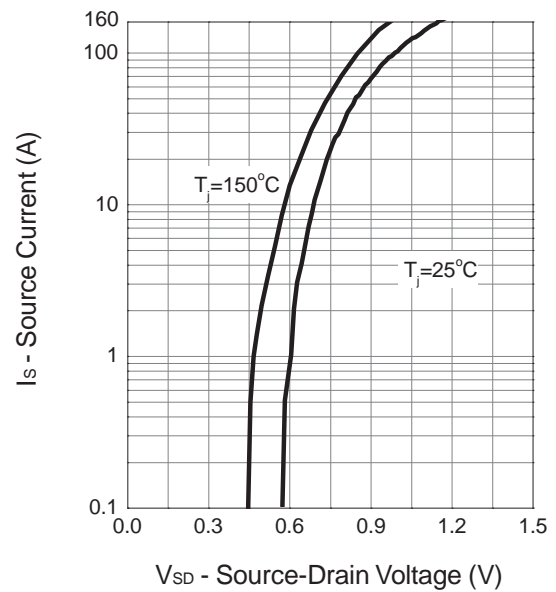


Typical Operating Characteristics (Cont.)

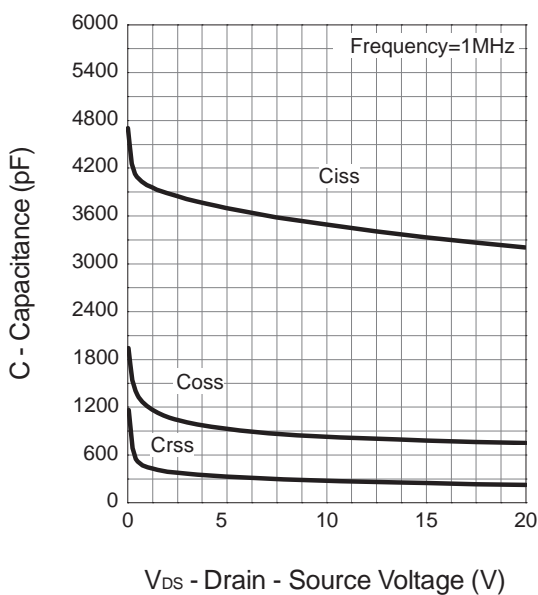
Drain-Source On Resistance



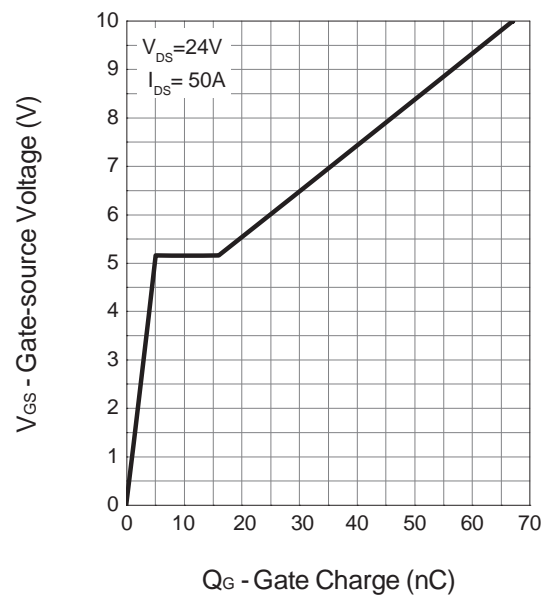
Source-Drain Diode Forward



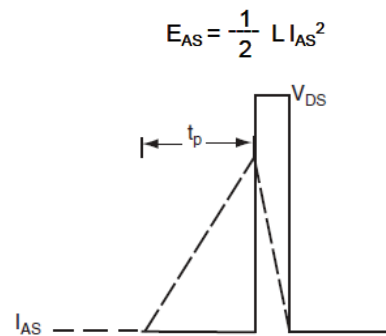
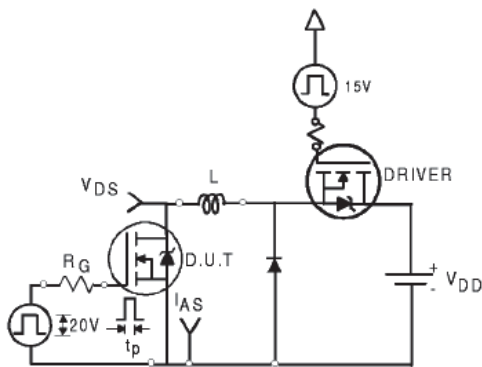
Capacitance



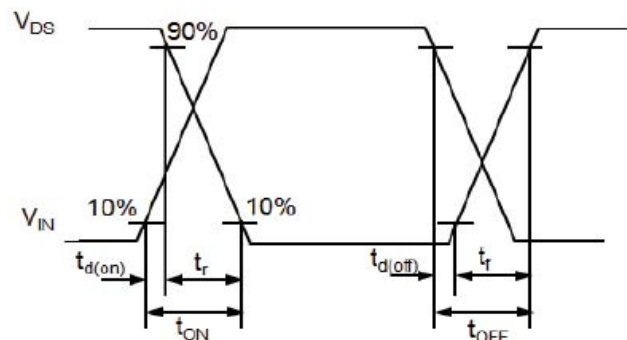
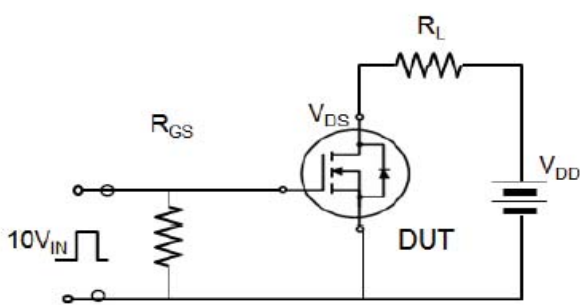
Gate Charge



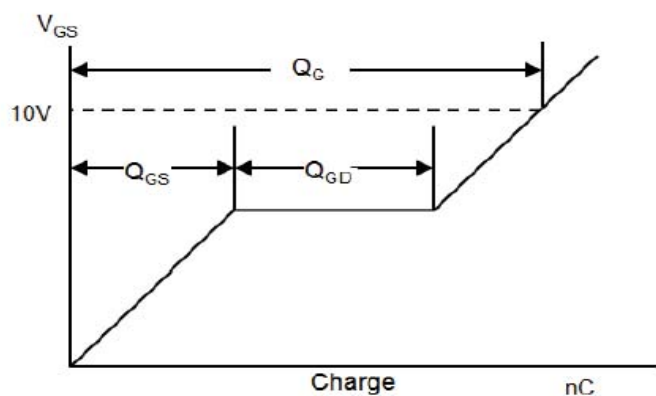
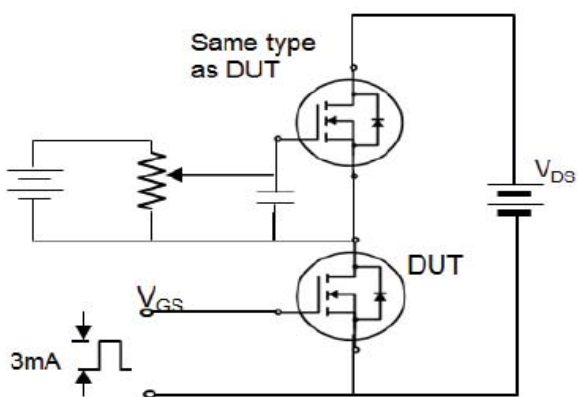
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit

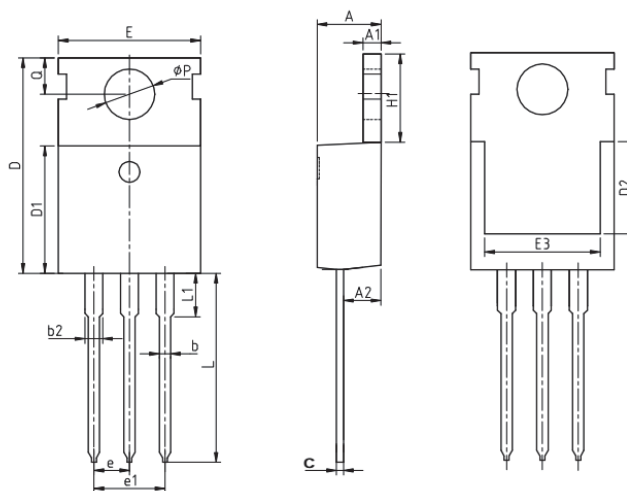


Device Per Unit

| Package Type | Unit | Quantity |
|--------------|------|----------|
| TO-220FB-3L | Tube | 50 |

Package Information

TO-220FB-3L



COMMON DIMENSIONS

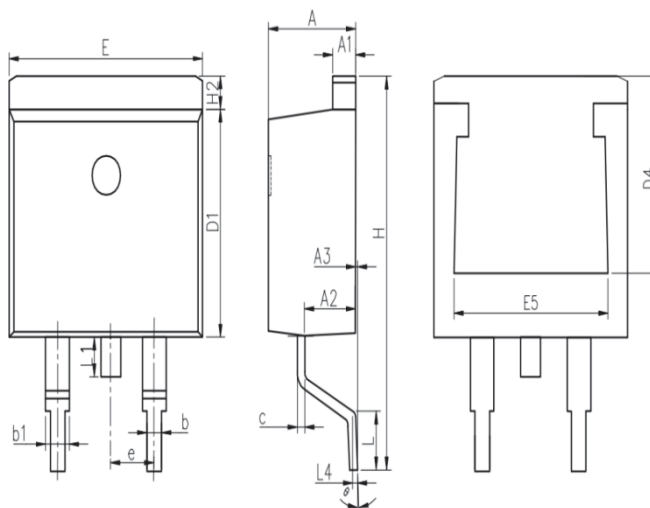
| SYMBOL | mm | | |
|--------|----------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.37 | 4.57 | 4.77 |
| A1 | 1.25 | 1.30 | 1.45 |
| A2 | 2.20 | 2.40 | 2.60 |
| b | 0.70 | 0.80 | 0.95 |
| b2 | 1.17 | 1.27 | 1.47 |
| c | 0.40 | 0.50 | 0.65 |
| D | 15.10 | 15.60 | 16.10 |
| D1 | 8.80 | 9.10 | 9.40 |
| D2 | 5.50 | - | - |
| E | 9.70 | 10.00 | 10.30 |
| E3 | 7.00 | - | - |
| e | 2.54 BSC | | |
| e1 | 5.08 BSC | | |
| H1 | 6.25 | 6.50 | 6.85 |
| L | 12.75 | 13.50 | 13.80 |
| L1 | - | 3.10 | 3.40 |
| ΦP | 3.40 | 3.60 | 3.80 |
| Q | 2.60 | 2.80 | 3.00 |

Device Per Unit

| Package Type | Unit | Quantity |
|--------------|------|----------|
| TO-263-2L | Reel | 50 |

Package Information

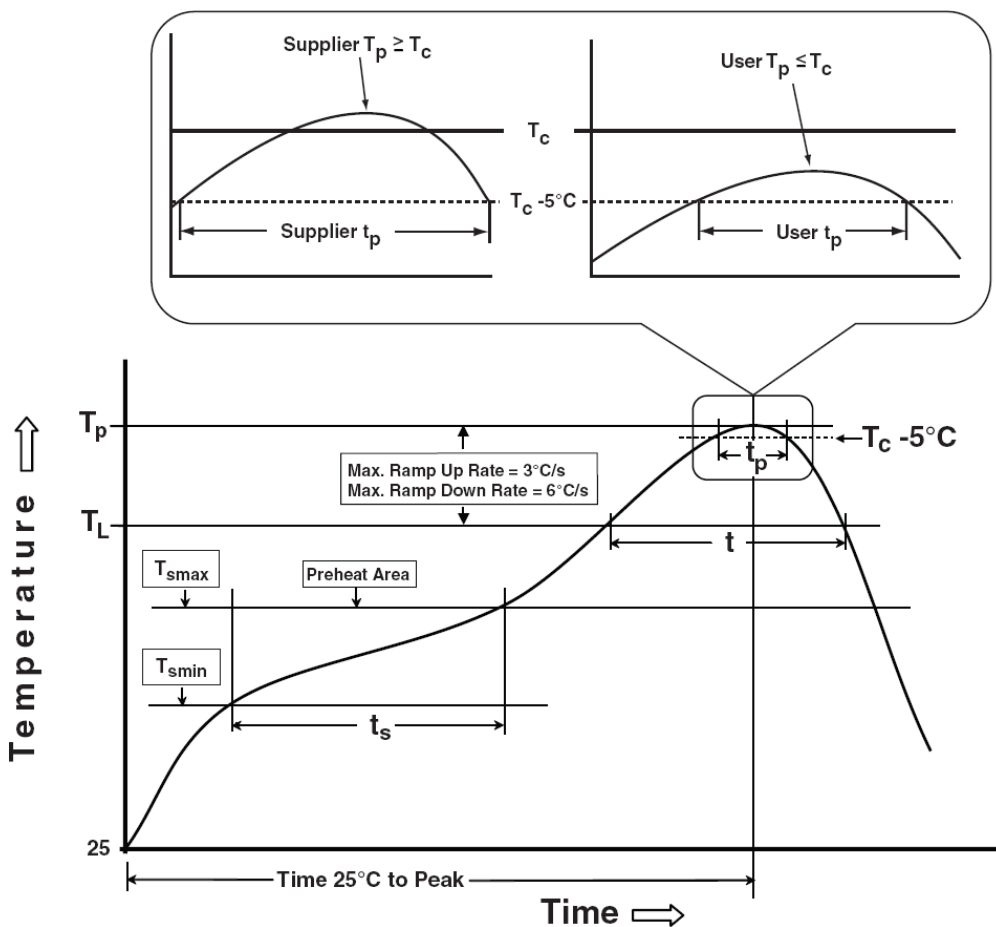
TO-263-2L



COMMON DIMENSIONS

| SYMBOL | mm | | |
|----------|----------|-------|-------|
| | MIN | NOM | MAX |
| A | 4.37 | 4.57 | 4.77 |
| A1 | 1.22 | 1.27 | 1.42 |
| A2 | 2.49 | 2.69 | 2.89 |
| A3 | 0 | 0.13 | 0.25 |
| b | 0.7 | 0.81 | 0.96 |
| b1 | 1.17 | 1.27 | 1.47 |
| c | 0.3 | 0.38 | 0.53 |
| D1 | 8.5 | 8.7 | 8.9 |
| D4 | 6.6 | - | - |
| E | 9.86 | 10.16 | 10.36 |
| E5 | 7.06 | - | - |
| e | 2.54 BSC | | |
| H | 14.7 | 15.1 | 15.5 |
| H2 | 1.07 | 1.27 | 1.47 |
| L | 2 | 2.3 | 2.6 |
| L1 | 1.4 | 1.55 | 1.7 |
| L4 | 0.25 BSC | | |
| θ | 0° | 5° | 9° |

Classification Profile



Classification Reflow Profiles

| Profile Feature | Sn-Pb Eutectic Assembly | Pb-Free Assembly |
|--|------------------------------------|------------------------------------|
| Preheat & Soak | | |
| Temperature min (T_{smin}) | 100 °C | 150 °C |
| Temperature max (T_{smax}) | 150 °C | 200 °C |
| Time (T_{smin} to T_{smax}) (t_s) | 60-120 seconds | 60-120 seconds |
| Average ramp-up rate (T_{smax} to T_p) | 3 °C/second max. | 3°C/second max. |
| Liquidous temperature (T_L) | 183 °C | 217 °C |
| Time at liquidous (t_l) | 60-150 seconds | 60-150 seconds |
| Peak package body Temperature (T_p)* | See Classification Temp in table 1 | See Classification Temp in table 2 |
| Time (t_p)** within 5°C of the specified classification temperature (T_c) | 20** seconds | 30** seconds |
| Average ramp-down rate (T_p to T_{smax}) | 6 °C/second max. | 6 °C/second max. |
| Time 25°C to peak temperature | 6 minutes max. | 8 minutes max. |
| * Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. | | |
| ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum. | | |

Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

| Package Thickness | Volume mm ³ <350 | Volume mm ³ ≥350 |
|-------------------|--------------------------------|--------------------------------|
| <2.5 mm | 235 °C | 220 °C |
| ≥2.5 mm | 220 °C | 220 °C |

Table 2. Pb-free Process – Classification Temperatures (Tc)

| Package Thickness | Volume mm ³ <350 | Volume mm ³ 350-2000 | Volume mm ³ >2000 |
|-------------------|--------------------------------|------------------------------------|---------------------------------|
| <1.6 mm | 260 °C | 260 °C | 260 °C |
| 1.6 mm – 2.5 mm | 260 °C | 250 °C | 245 °C |
| ≥2.5 mm | 250 °C | 245 °C | 245 °C |

Reliability Test Program

| Test item | Method | Description |
|---------------|---------------|----------------------------------|
| SOLDERABILITY | JESD-22, B102 | 5 Sec, 245°C |
| HOLT | JESD-22, A108 | 168Hrs/500Hrs/1000Hrs,Bias@125°C |
| PCT | JESD-22, A102 | 96 Hrs, 100%RH, 2atm, 121°C |
| TCT | JESD-22, A104 | 500 Cycles, -55°C~150°C |

Customer Service

Worldwide Sales and Service: sales@hymexa.com

Technical Support:Technology@hymexa.com

Xi'an Huayi Microelectronics Co., Ltd.

No.8928,Shangji Road,Economic and Technological Development Zone,Xi'an,China

TEL: (86-029) 86685706

FAX: (86-029) 86685705

E-mail: sales@hymexa.com

Web net: www.hymexa.com